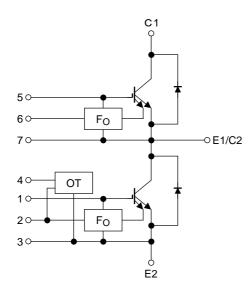
TOSHIBA IGBT Module Silicon N Channel IGBT

# **MG400Q2YS60A**

# High Power Switching Applications Motor Control Applications

- Integrates a complete half bridge power circuit and fault-signal output circuit in one package. (short circuit and over temperature)
- The electrodes are isolated from case.
- Low thermal resistance.
- VCE (sat) = 2.4 V (typ.)

## **Equivalent Circuit**

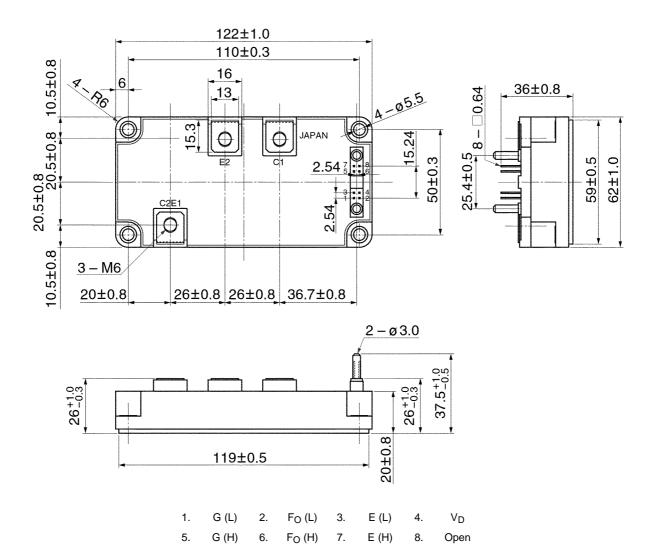


#### Signal terminal

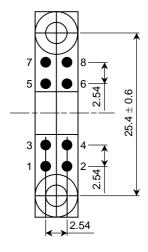
- 1. G (L) 2.  $F_O$  (L) 3. E (L) 4.  $V_D$ 
  - G (H) 6. F<sub>O</sub> (H) 7. E (H) 8. Open

## Package Dimensions: 2-123C1B

Unit: mm



# **Signal Terminal Layout**



- 1. G (L)
- 2. F<sub>O</sub> (L)
- 3. E(L)
- 4. V<sub>D</sub>
- 5. G (H)
- 6. F<sub>O</sub> (H)
- 7. E (H)
- 8. Open

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Weight: 375 g

## **Maximum Ratings (Ta = 25°C)**

Stage	Characteristics	Symbol	Rating	Unit		
	Collector-emitter voltage	V <sub>CES</sub>	1200	V		
	Gate-emitter voltage	Gate-emitter voltage			V	
	Collector current	DC	Ic	400	Α	
Inverter	Collector current	1 ms	I <sub>CP</sub>	800	A	
		DC	I <sub>F</sub>	400	А	
	Forward current	1 ms	I <sub>FM</sub>	800	А	
	Collector power dissipation (Tc =	Collector power dissipation (Tc = 25°C)			W	
	Control voltage (OT)	$V_{D}$	20	V		
Control	Fault input voltage	VFO	20	V		
	Fault input current	IFO	20	mA		
	Junction temperature	Tj	150	°C		
Module	Storage temperature range	T <sub>stg</sub>	-40~125	°C		
	Operation temperature range	T <sub>ope</sub>	-20~100	°C		
	Isolation voltage	V <sub>isol</sub>	2500 (AC 1 min)	V		
	Screw torque	_	3 (M5)	N·m		

# Electrical Characteristics ( $T_j = 25^{\circ}C$ )

## 1. Inverter stage

Characteristics		Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage current		I <sub>GES</sub>	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0$		_	_	+3/-4	mA
			V <sub>GE</sub> = +10 V, V <sub>CE</sub> = 0		_	_	100	nA
Collector cut-off current		I <sub>CES</sub>	V <sub>CE</sub> = 1200 V, V <sub>GE</sub> = 0		_	_	1.0	mA
Gate-emitter cut-off voltage		V <sub>GE (off)</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 400 mA		6.0	7.0	8.0	V
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 400 A	Tj = 25°C	_	2.4	2.8	V
				Tj = 125°C	_	_	3.2	
Input capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 10 V, V <sub>GE</sub> = 0, f = 1 MHz		_	31000	_	pF
	Turn-on delay time	t <sub>d (on)</sub>			0.10	_	1.00	
Switching time	Turn-off time	t <sub>off</sub>	`		_	_	2.00	6
	Fall time	t <sub>f</sub>		t <sub>f</sub> (Note 1) (Note 1)	_	_	0.50	μS
Reverse recovery time		t <sub>rr</sub>	(				0.50	
Forward voltage		V <sub>F</sub>	I <sub>F</sub> = 400 A		_	2.4	2.8	V

Note 1: Switching time test circuit & timing chart

## 2. Control (Tc = 25°C)

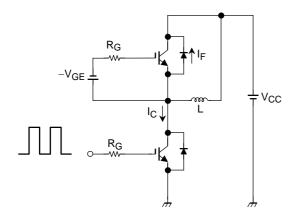
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Fault output current	ОС	V <sub>GE</sub> = 15 V	480	_	_	Α
Over temperature	ОТ	_	100	_	125	°C
Fault output delay time	t <sub>d (Fo)</sub>	$V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$	_	_	8	μS



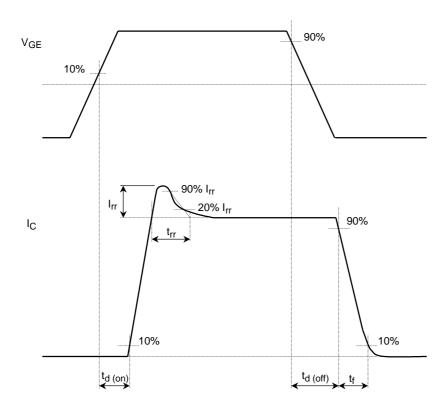
## 3. Module (Tc = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Junction to case thermal resistance	R <sub>th (j-c)</sub>	Inverter IGBT stage	_	_	0.033	°C/W	
Junction to case thermal resistance		Inverter FRD stage	_	_	0.068		
Case to fin thermal resistance	R <sub>th (c-f)</sub>	With silicon compound		0.013		°C/W	

# **Switching Time Test Circuit**



# **Timing Chart**



## Remark

## <Short circuit capability condition >

- Short circuit capability is 6 μs after fault output signal. Please keep following condition to use fault output signal.
  - VCC ≤ 750 V
  - $14.8 \text{ V} \le \text{VGE} \le 17.0 \text{ V}$
  - $RG \ge 5.1 \Omega$
  - $T_j \leq 125$ °C

## <Gate voltage >

• To use this product, VGE must be provided higher than 14.8 V In case VGE is less than 14.8 V, fault signal FO may not be output even under error conditions.

#### <For parallel use>

• For parallel use of this product, please use the same rank for both VCE (sat) and VF among IGBT in parallel without fail.

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V <sub>CE</sub> (sat)	V <sub>F</sub>	Min	Max
24	E	2.1	2.4
26	F	2.3	2.6
28	G	2.5	2.8

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